CRSM027N08N4

SkyMOS4 N-MOSFET 80V, 2.5mΩ, 189A

Features

- Uses CRM(CQ) advanced SkyMOS4 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent QgxRDS(on) product(FOM)
- Qualified according to JEDEC criteria

Applications

- Synchronous Rectification for AC/DC Quick Charger
- UPS (uninterrupible Power Supplies)

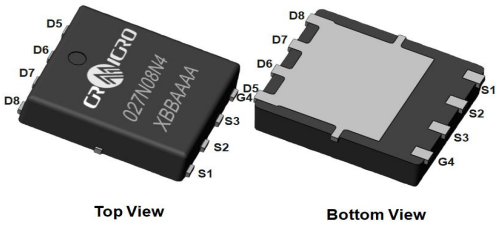
Product Summary

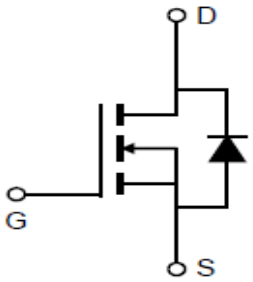
V_{DS}	80V
$R_{DS(on)@10V\ typ}$	2.5mΩ
I_D	189A

100% Avalanche Tested
100% DVDS Tested

RoHS HF

DFN5*6 Cu Clip Bond





Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRSM027N08N4	027N08N4	DFN5X6 clip	Tape&Reel	N/A	N/A	5000pcs

Absolute Maximum Ratings

Parameter	**Symbol**	**Value**	**unit**
Drain-source voltage	V_{DS}	80	V
Continuous drain current T_C = 25°C T_C = 100°C	I_D	 189 120	A
Pulsed drain current (TC = 25°C, tp limited by Tjmax)	ID pulse	756	A
Avalanche energy, single pulse (ID=29A, Rg=25Ω)	E_{AS}	130	mJ
Gate-Source voltage	V_{GS}	±20	V
Power dissipation (T_C = 25°C)	P_{tot}	156	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	Tsold	260	°C

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Thermal Resistance

Parameter	Symbol	Value			unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	RthJC	-	0.5	0.80	°C/W	-
Thermal resistance, junction - ambient(min. footprint)	RthJA	-	-	55	°C/W	-

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	**Symbol**	**Value**			**unit**	**Test Condition**
		min.	**typ.**	**max.**		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	80	-	-	V	VGS=0V, ID=250μA
Gate threshold voltage	$V_{GS(th)}$	2.2	3	3.8	V	VDS=VGS,ID=250μA
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	V_{DS}=80V,V_{GS}=0V T_j=25°C
		-	-	100		T_j=125°C
Gate-source leakage current	I_{GSS}		-	±100	nA	V_{GS}=±20V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	2	2.5	3.0	mΩ	VGS=10V,I_D=50A
		2.08	2.6	3.8	mΩ	VGS=8V,I_D=40A
Transconductance	g_{fs}	90.4	113	146.9	S	V_{DS}=5V,I_D=50A
Dynamic Characteristic						
Input Capacitance	C_{iss}	3680	5520	8280	pF	V_{GS}=0V, V_{DS}=40V, f=1MHz
Output Capacitance	C_{oss}	660	990	1485		
Reverse Transfer Capacitance	C_{rss}	21	32	64		
Gate Total Charge	Q_G	51	76	114	nC	V_{GS}=10V, V_{DS}=40V, I_D=50A, f=1MHz
Gate-Source charge	Q_{gs}	20	30	45		
Gate-Drain charge	Q_{gd}	6	9	18		
Turn-on delay time	$t_{d(on)}$	14	21	32	ns	V_{GS}=10V, V_{DD}=40V, R_{G_ext}=2.7Ω
Rise time	t_r	61	92	137		
Turn-off delay time	$t_{d(off)}$	30	45	68		
Fall time	t_f	63	94	141		
Gate resistance	R_G	1.2	1.8	2.6	Ω	V_{GS}=0V, V_{DS}=0V, f=1MHz

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Body Diode Characteristic

Parameter	Symbol	Value			unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	0.5	0.8	1.4	V	V_{GS}=0V,I_{SD}=50A
Body Diode Continuous Forward Current	Is	-	-	189	A	TC = 25°C
Body Diode Pulsed Current	IS pulse	-	-	756	A	TC = 25°C
Body Diode Reverse Recovery Time	t_{rr}	49	74	147	ns	IF=50A, dI/dt=100A/μs
Body Diode Reverse Recovery Charge	Q_{rr}	74	111	223	nC	

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Typical Performance Characteristics

Fig 1: Output Characteristics

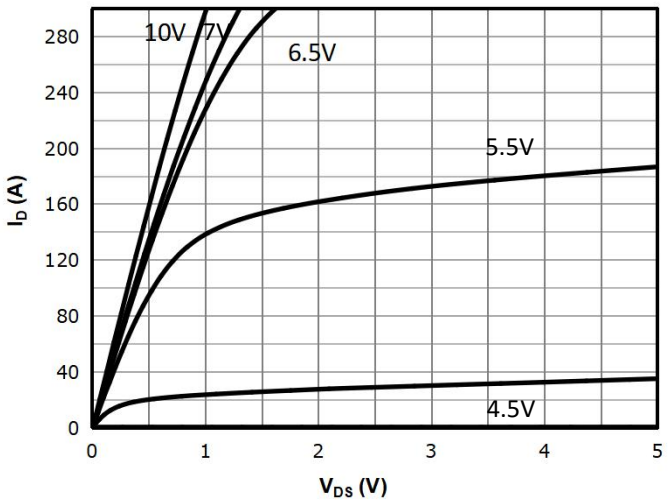


Fig 2: Transfer Characteristics

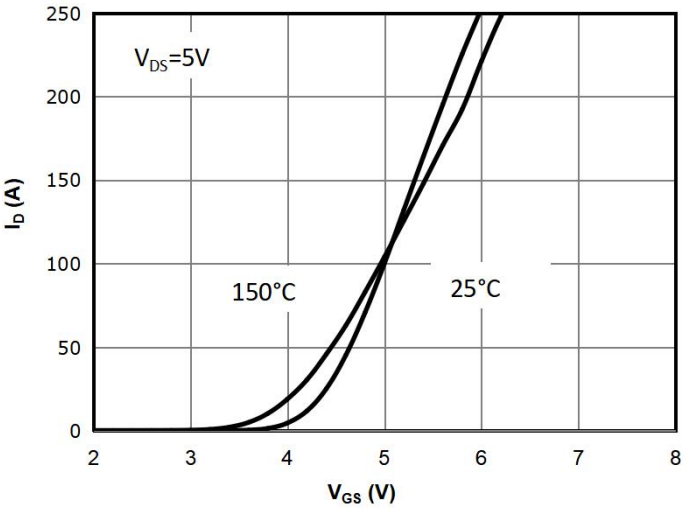


Fig 3: Rds(on) vs Drain Current and Gate Voltage

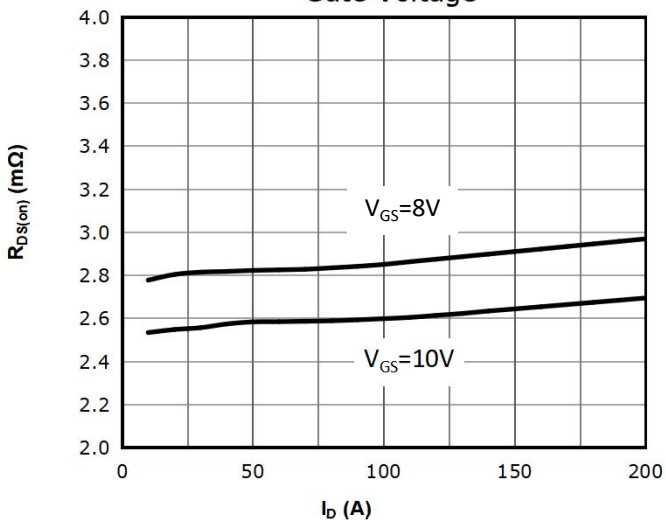


Fig 4: Rds(on) vs Gate Voltage

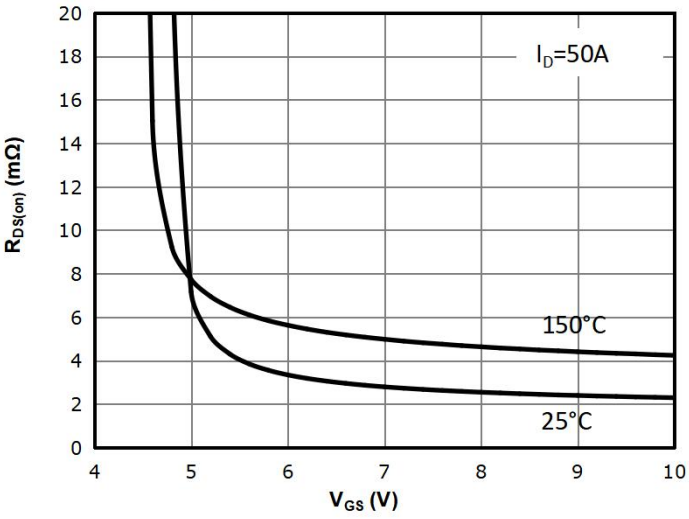


Fig 5: Rds(on) vs. Temperature

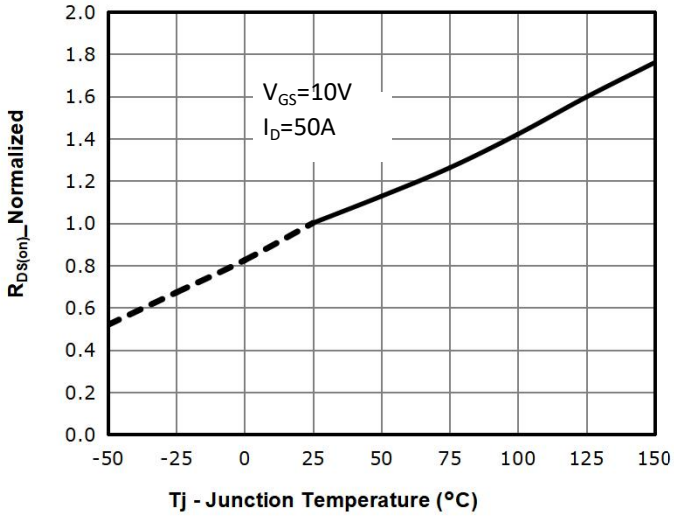
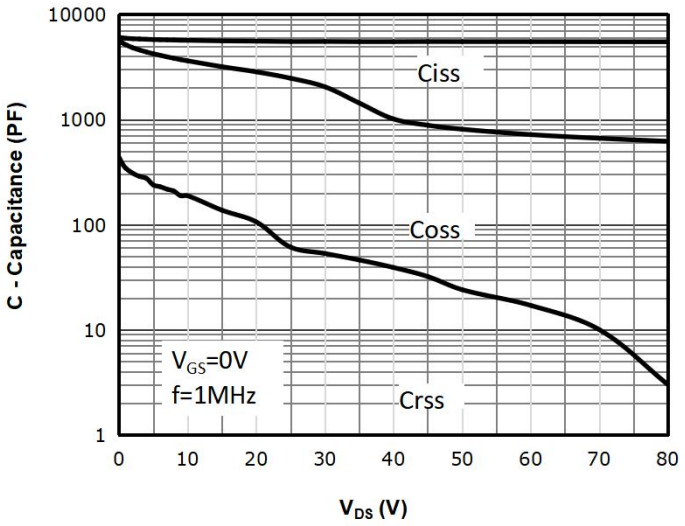


Fig 6: Capacitance Characteristics



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Fig 7: Gate Charge Characteristics

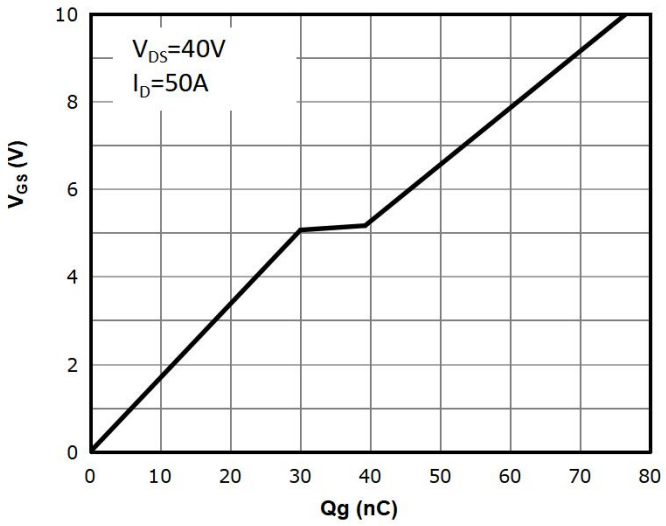


Fig 8: Body-diode Forward Characteristics

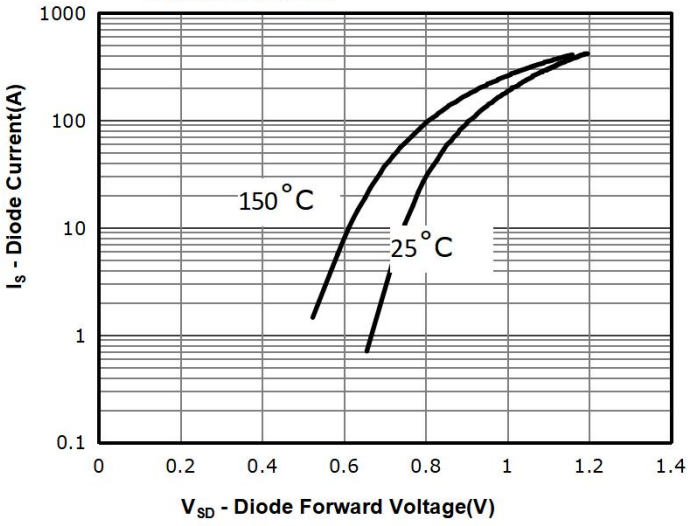


Fig 9: Power Dissipation

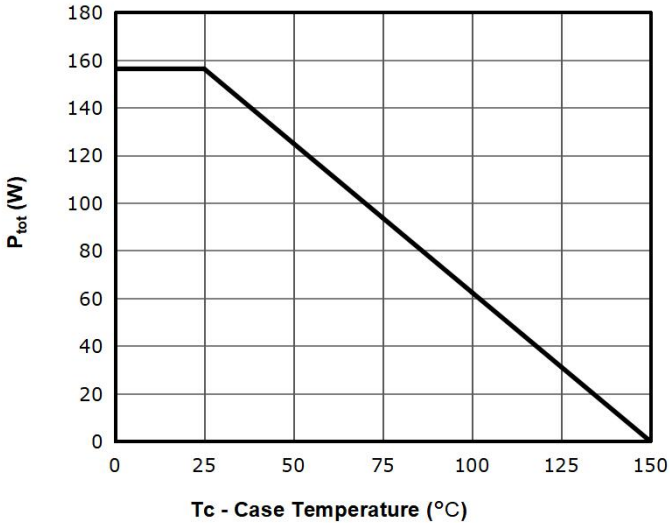


Fig 10: Drain Current Derating

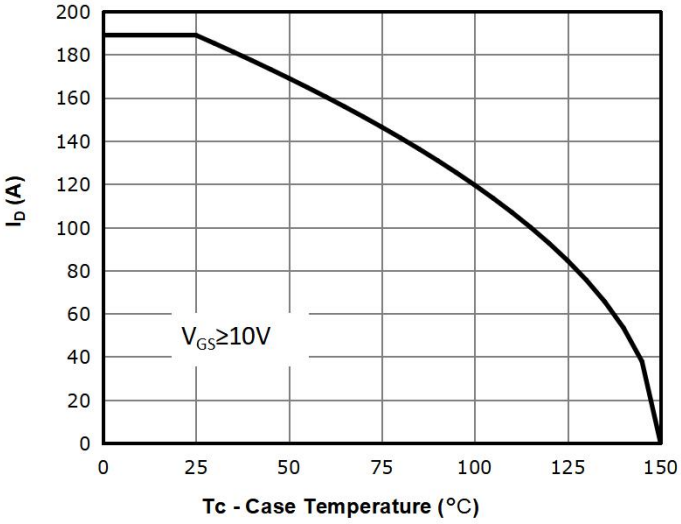


Fig 11: BVds vs. Temperature

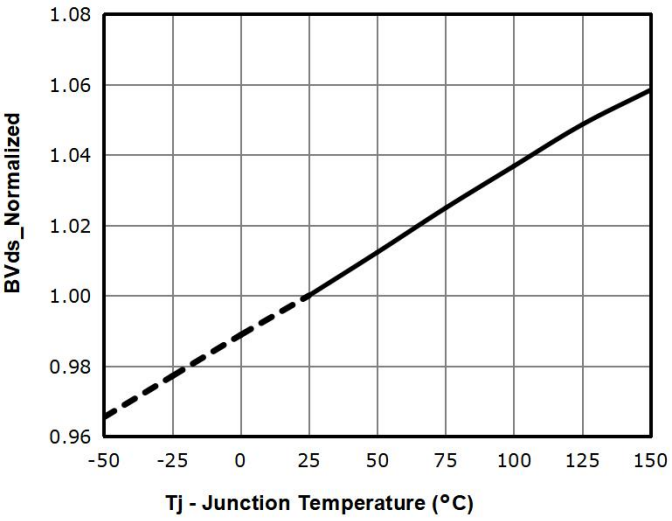
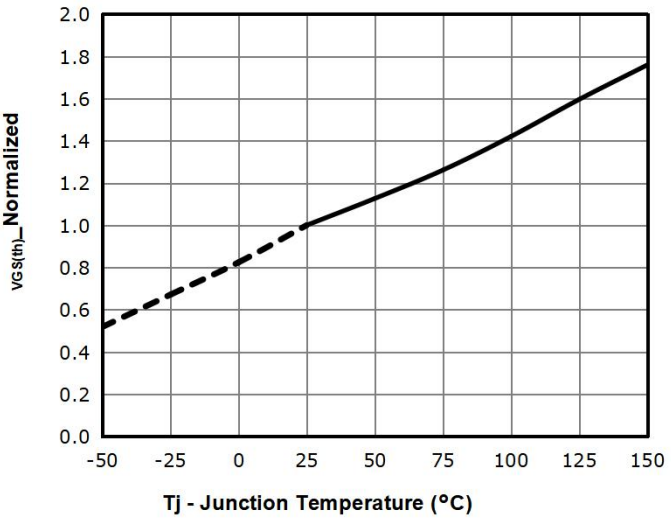


Fig 12: VGS(th) vs. Temperature



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Fig 13: Safe Operating Area

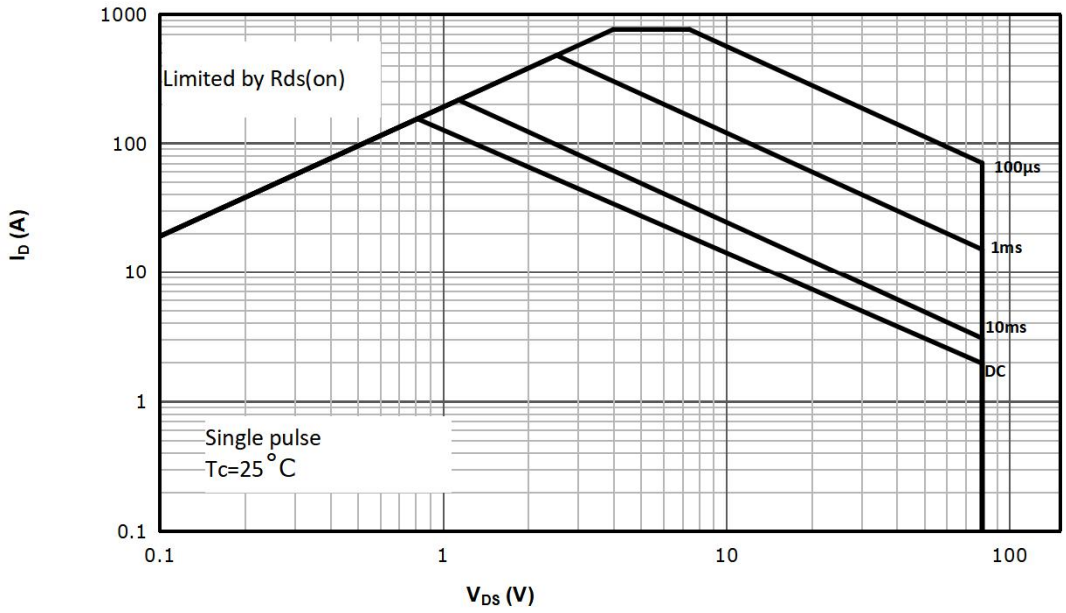
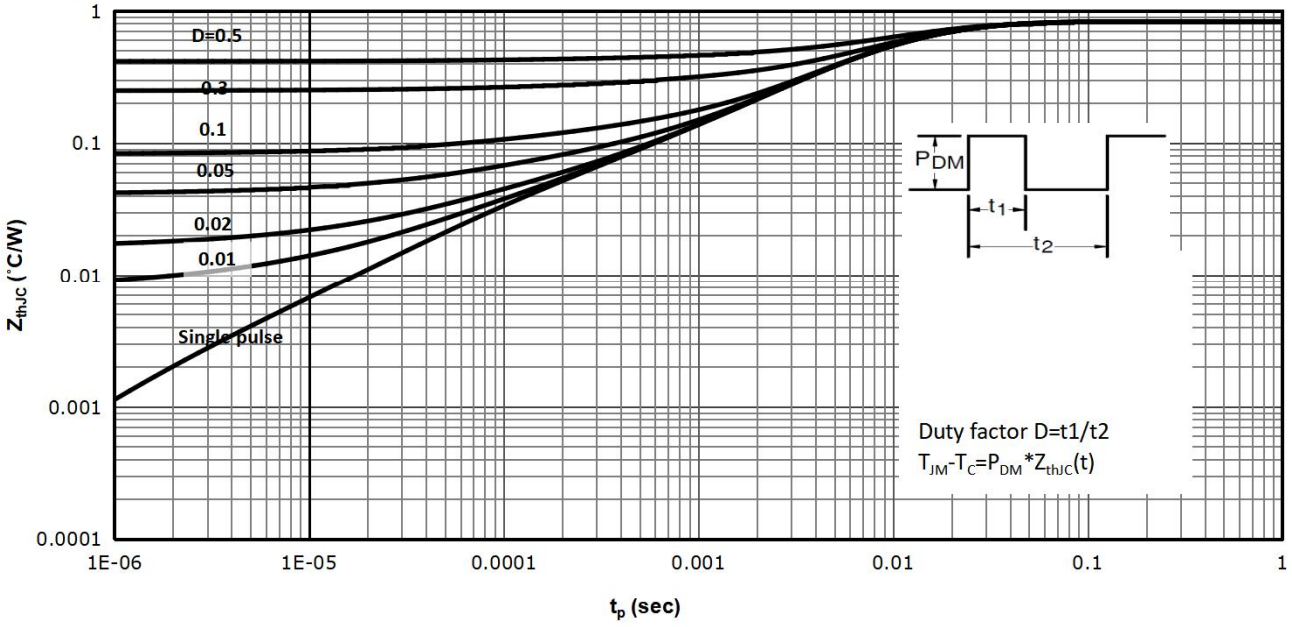


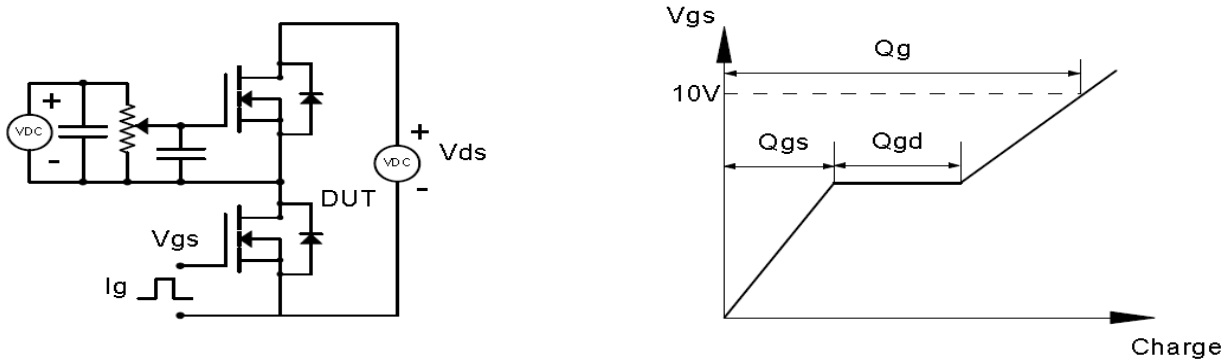
Fig 14: Max. Transient Thermal Impedance



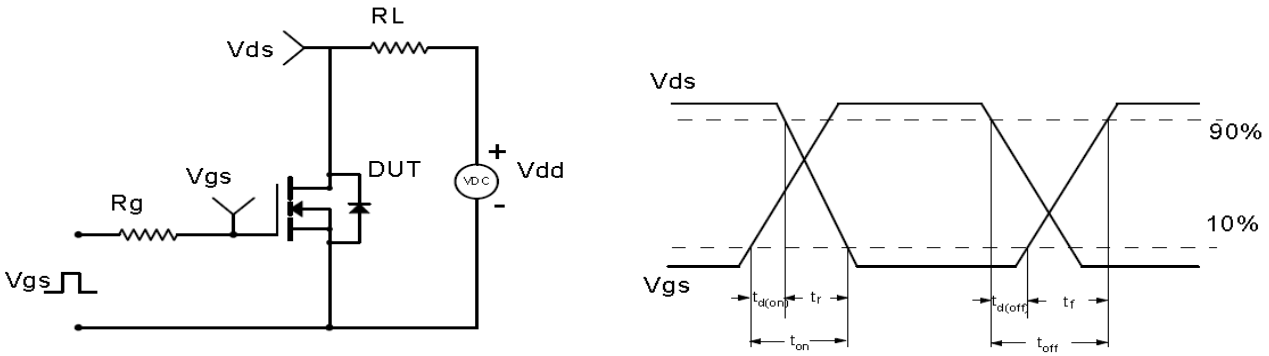
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Test Circuit & Waveform

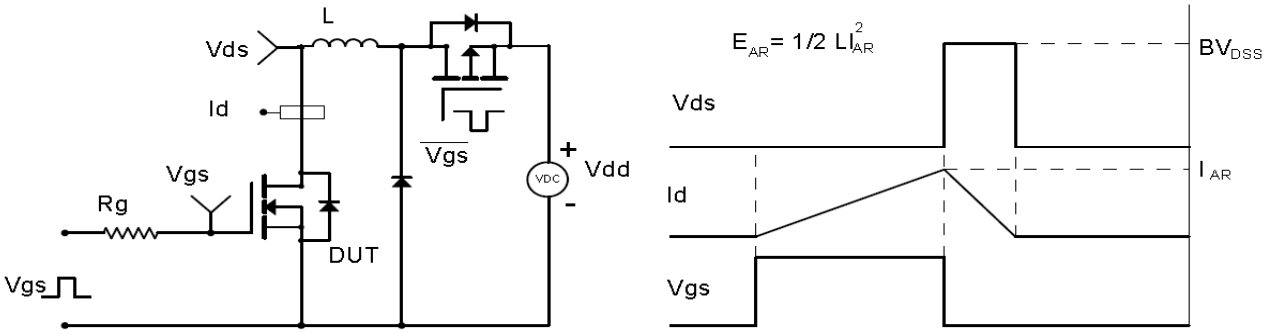
Gate Charge Test Circuit & Waveform



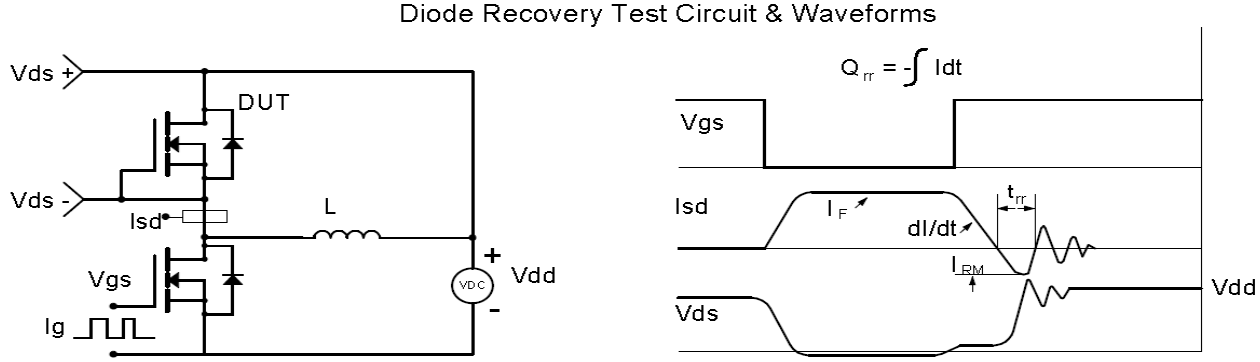
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

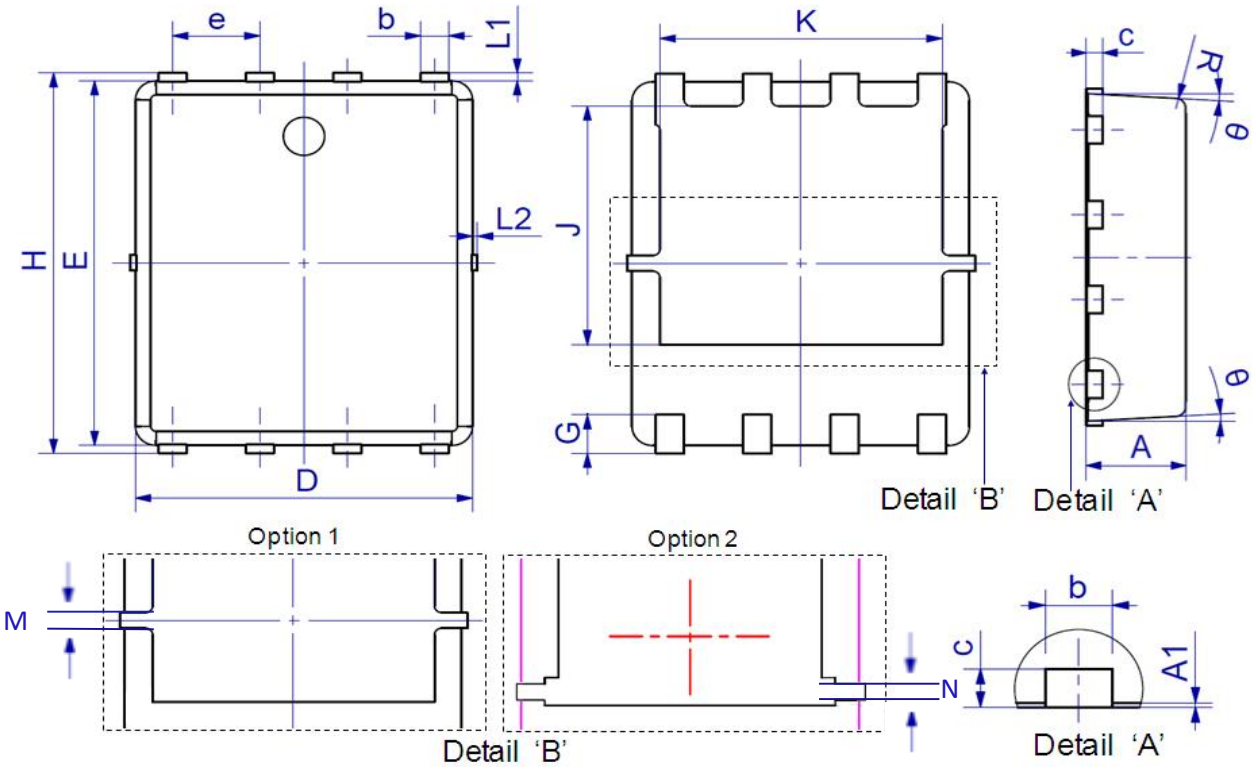


Diode Recovery Test Circuit & Waveforms



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Package Outline: DFN5X6



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.80	1.20	0.031	0.047
A1	0.00	0.05	0.000	0.002
b	0.30	0.51	0.012	0.020
c	0.15	0.35	0.006	0.014
D	4.80	5.40	0.189	0.213
e	1.27 BSC		0.050 BSC	
E	5.66	6.06	0.223	0.239
G	0.30	0.71	0.012	0.028
H	5.90	6.35	0.232	0.250
J	3.32	3.92	0.131	0.154
K	3.61	4.25	0.142	0.167
L1	0.05	0.25	0.002	0.010
L2	0.00	0.15	0.000	0.006
M	0.10	0.40	0.004	0.016
N	0.25	0.25	0.010	0.010
R	0.25 REF		0.010 REF	
θ	0°	12°	0°	12°

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Marking



NOTE:
XBBAAAA
X —Assembly location code
BB —Fab code
AAAA —Lot code

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Revision History

Revison	Date	Major changes
1.0	2020/2/24	Release of Preliminary Version.
2.0	2023/7/6	Revise Marking&Qty&$RDS_{(on)}$@10V

Disclaimer

unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.

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